

***Amendments to the Specification***

Please add the following paragraph between current paragraphs [0029] and [0030]:

Based on the description provided herein, it would also be evident to one of skill in the art to substitute MOS-on-PWELL devices for the MOS-on-NWELL devices and NMOS transistors for the PMOS transistors. Specifically, in light of the description provided herein, it would be evident to one of skill in the art that a capacitor can be made from: a first MOS-on-PWELL device formed on a substrate and having a first pickup terminal and a first gate; a second MOS-on-PWELL device formed on the substrate and having a second pickup terminal and a second gate, wherein the first gate is connected to the second pickup terminal and wherein the second gate is connected to the first pickup terminal, a first NMOS transistor formed on the substrate and having its source and drain terminals connected together; and a second NMOS transistor formed on the substrate and having its source and drain terminals connected together, wherein a gate of the first NMOS transistor is connected to the source and drain terminals of the second NMOS transistor, wherein a gate of the second NMOS transistor is connected to the source and drain terminals of the first NMOS transistor, and wherein a combination of the first and second NMOS transistors are connected in parallel with the first and second MOS-on-PWELL devices.